

isc Silicon NPN Power Transistor

BU932RPFI

DESCRIPTION

- · High Voltage
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

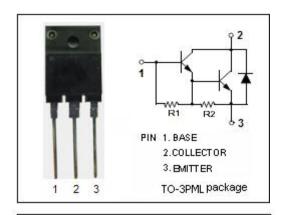
- · High ruggedness electronic ignitions
- · High voltage ignition coil driver

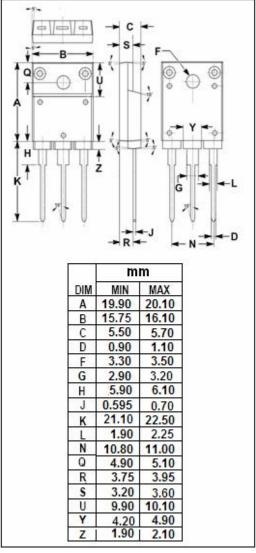


| ABSOLUTE MAXIMUM RATINGS (T _a =25℃) | | | | | | | | |
|--|--|---------|---------------|--|--|--|--|--|
| SYMBOL | PARAMETER | VALUE | UNIT | | | | | |
| V_{CBO} | Collector-Base Voltage | 500 | V | | | | | |
| Vceo | Collector-Emitter Voltage | 450 | V | | | | | |
| V _{EBO} | Emitter-Base Voltage | 5 | V | | | | | |
| Ic | Collector Current | 15 | Α | | | | | |
| I _{CM} | Collector Current-peak | 30 | Α | | | | | |
| I _B | Base Current | 1 | Α | | | | | |
| I _{BM} | Base Current-peak | 5 | Α | | | | | |
| Pc | Collector Power Dissipation @T _C =25°C | 60 | W | | | | | |
| T _j | Junction Temperature 150 | | $^{\circ}$ | | | | | |
| T _{stg} | Storage Temperature Range | -40~150 | ${\mathbb C}$ | | | | | |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|---------------------|--------------------------------------|------|------|
| R _{th j-c} | Thermal Resistance, Junction to Case | 2.08 | °C/W |







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ELECTRICAL CHARACTERISTICS

Tc=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|-----------------------|--------------------------------------|---|-----|------|------------|------|
| V _{CEO(SUS)} | Collector-Emitter Sustaining Voltage | I _C = 50mA; I _B = 0 | 450 | | | V |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = 8 A; I _B = 150mA | | | 1.8 | V |
| V _{BE(sat)} | Base-Emitter Saturation Voltage | I _C = 8 A; I _B = 150mA | | | 2.2 | V |
| I _{CES} | Collector Cutoff Current | V _{CE} = 500V;V _{BE} = 0 V _{CE} = 500V;V _{BE} = 0;T _j = 125°C | | | 1.0 5.0 | mA |
| I _{CEO} | Collector Cutoff Current | V _{CE} = 450V;I _B = 0 | | | 1.0 | mA |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = 5V; I _C = 0 | | | 50 | mA |
| h _{FE} | DC Current Gain | I _C = 5A; V _{CE} = 10V | 300 | | | |
| V _{ECF} | C-E Diode Forward Voltage | I _F = 10A | | | 2.8 | V |

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